

# LDO Regulator - Very Low Dropout, CMOS, Bias Rail

### **NCP136**

The NCP136 is a 700 mA VLDO equipped with NMOS pass transistor and a separate bias supply voltage (V<sub>BIAS</sub>). The device provides very stable, accurate output voltage with low noise suitable for space constrained, noise sensitive applications. In order to optimize performance for battery operated portable applications, the NCP136 features low  $I_Q$  consumption. The WLCSP6 1.4 mm x 0.8 mm Chip Scale package is optimized for use in space constrained applications.

#### **Features**

- Input Voltage Range: V<sub>OUT</sub> to 5.5 V
- Bias Voltage Range: 2.5 V to 5.5 V
- Fixed or Adjustable Voltage Version Available
- Output Voltage Range: 0.4 V to 1.8 V (Fixed)
- Output Voltage Range: 0.4 V to 3.0 V (Adjustable)
- ±1% Accuracy over Temperature, 0.5% V<sub>OUT</sub> @ 25°C
- Ultra-Low Dropout: Typ. 40 mV at 700 mA
- Very Low Bias Input Current of Typ. 80 μA
- Very Low Bias Input Current in Disable Mode: Typ. 0.5 μA
- Logic Level Enable Input for ON/OFF Control
- Output Active Discharge Option Available
- Stable with a 10 μF Ceramic Capacitor
- Available in WLCSP6 1.4 mm x 0.8 mm, 0.4 mm pitch Package
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- Battery-powered Equipment
- Smartphones, Tablets
- Cameras, DVRs, STB and Camcorders

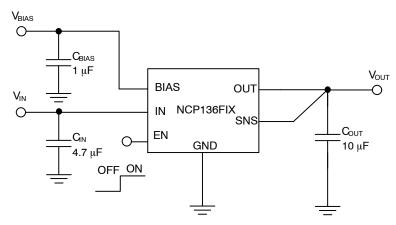


Figure 1. Typical Application Schematic - Fixed Voltage Version



WLCSP6, 1.4x0.8x0.33 CASE 567XK



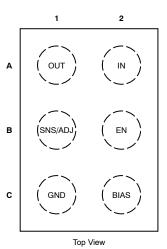
WLCSP6, 1.4x0.8x0.37 CASE 567YU

#### MARKING DIAGRAM



XX = Specific Device Code
M = Month Code

#### **PIN CONNECTIONS**



#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 12 of this data sheet.

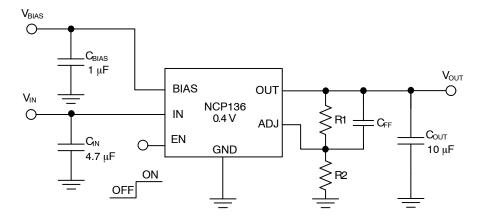
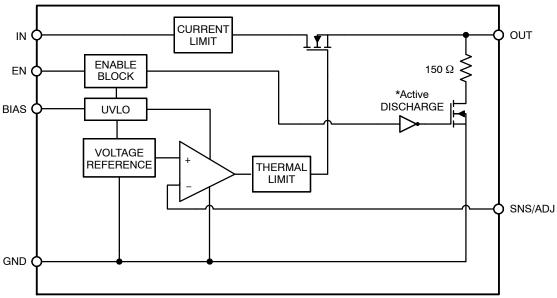


Figure 2. Typical Application Schematic – Adjustable Voltage Version



\*Active output discharge function is present only in NCP136A and NCP136C option devices.

Figure 3. Simplified Schematic Block Diagram

#### PIN FUNCTION DESCRIPTION

| Pin No.<br>WLCSP6 | Pin Name | Description  |
|-------------------|----------|--|
| A1                | OUT      | Regulated Output Voltage pin   |
| A2                | IN       | Input Voltage Supply pin   |
| B1                | SNS/ADJ  | Feedback / adjustable input pin (connect this pin directly to the OUT pin or to the resistor divider)                |
| B2                | EN       | Enable pin. Driving this pin high enables the regulator. Driving this pin low puts the regulator into shutdown mode. |
| C1                | GND      | Ground pin   |
| C2                | BIAS     | Bias voltage supply for internal control circuits. This pin is monitored by internal Under-Voltage Lockout Circuit.  |

#### **ABSOLUTE MAXIMUM RATINGS**

| Rating                                    | Symbol   | Value                          | Unit |
|---|--|--------------------------------|------|
| Input Voltage (Note 1)                    | V <sub>IN</sub>  | -0.3 to 6                      | V    |
| Output Voltage                            | V <sub>OUT</sub>   | $-0.3$ to $(V_{IN}+0.3) \le 6$ | V    |
| Chip Enable, Bias and SNS Input           | V <sub>EN</sub> , V <sub>BIAS</sub> , V <sub>SNS/ADJ</sub> | -0.3 to 6                      | ٧    |
| Output Short Circuit Duration             | t <sub>SC</sub>  | unlimited                      | s    |
| Maximum Junction Temperature              | T <sub>J</sub>   | 150                            | °C   |
| Storage Temperature                       | T <sub>STG</sub>   | -55 to 150                     | °C   |
| ESD Capability, Human Body Model (Note 2) | ESD <sub>HBM</sub>   | 2000                           | V    |
| ESD Capability, Machine Model (Note 2)    | ESD <sub>MM</sub>  | 200                            | V    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHĂRACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
- 2. This device series incorporates ESD protection (except OUT pin) and is tested by the following methods:

ESD Human Body Model tested per EIA/JESD22-A114

ESD Machine Model tested per EIA/JESD22-A115

Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

#### THERMAL CHARACTERISTICS

| Rating   | Symbol          | Value | Unit |
|--|-----------------|-------|------|
| Thermal Characteristics, WLCSP6 1.4 mm x 0.8 mm Thermal Resistance, Junction-to-Air (Note 3) | $R_{\theta JA}$ | 69    | °C/W |

<sup>3.</sup> This junction—to—ambient thermal resistance under natural convection was derived by thermal simulations based on the JEDEC JESD51 series standards methodology. Only a single device mounted at the center of a high\_K (2s2p) 80 mm x 80 mm multilayer board with 1–ounce internal planes and 2–ounce copper on top and bottom. Top copper layer has a dedicated 1.6 sqmm copper area.

**ELECTRICAL CHARACTERISTICS**  $-40^{\circ}C \le T_J \le 85^{\circ}C$ ;  $V_{BIAS} = 2.7 \text{ V or } (V_{OUT} + 1.6 \text{ V})$ , whichever is greater,  $V_{IN} = V_{OUT(NOM)} + 0.3 \text{ V}$ ,  $I_{OUT} = 1 \text{ mA}$ ,  $V_{EN} = 1 \text{ V}$ ,  $C_{IN} = 4.7 \text{ }\mu\text{F}$ ,  $C_{OUT} = 10 \text{ }\mu\text{F}$ ,  $C_{BIAS} = 1 \text{ }\mu\text{F}$ , unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . Min/Max values are for  $-40^{\circ}C \le T_J \le 85^{\circ}C$  unless otherwise noted. (Note 4)

| Parameter                         | Test Conditions   | Symbol                   | Min                                   | Тур        | Max  | Unit          |
|-----------------------------------|---|--------------------------|---------------------------------------|------------|------|---------------|
| Operating Input Voltage<br>Range  |   | V <sub>IN</sub>          | V <sub>OUT</sub> +<br>V <sub>DO</sub> |            | 5.5  | V             |
| Operating Bias Voltage<br>Range   |   | V <sub>BIAS</sub>        | (V <sub>OUT</sub> + 1.50) ≥ 2.5       |            | 5.5  | V             |
| Undervoltage Lock-out             | V <sub>BIAS</sub> Rising<br>Hysteresis  | UVLO                     |                                       | 1.6<br>0.2 |      | V             |
| Output Voltage Accuracy           |   | V <sub>OUT</sub>         |                                       | ±0.5       |      | %             |
| Output Voltage Accuracy           | $\begin{array}{l} -40^{\circ}C \leq T_{J} \leq 85^{\circ}C,\ V_{OUT(NOM)} + 0.1\ V \leq V_{IN} \leq V_{OUT(NOM)} \\ +\ 1.0\ V,\ 2.7\ V\ or\ (V_{OUT(NOM)} + 1.6\ V),\ whichever\ is \\ greater < V_{BIAS} < 5.5\ V,\ 1\ mA < I_{OUT} < 700\ mA \end{array}$ | V <sub>OUT</sub>         | -1.0                                  |            | +1.0 | %             |
| V <sub>IN</sub> Line Regulation   | $V_{OUT(NOM)} + 0.1 \text{ V} \le V_{IN} \le 5.0 \text{ V}$   | Line <sub>Reg</sub>      |                                       | 0.01       |      | %/V           |
| V <sub>BIAS</sub> Line Regulation | 2.7 V or (V $_{OUT(NOM)}$ + 1.6 V), whichever is greater < $V_{BIAS}$ < 5.5 V   | Line <sub>Reg</sub>      |                                       | 0.01       |      | %/V           |
| Load Regulation                   | I <sub>OUT</sub> = 1 mA to 700 mA   | Load <sub>Reg</sub>      |                                       | 1.5        |      | mV            |
| V <sub>IN</sub> Dropout Voltage   | I <sub>OUT</sub> = 700 mA (Note 5)  | $V_{DO}$                 |                                       | 40         | 60   | mV            |
| V <sub>BIAS</sub> Dropout Voltage | I <sub>OUT</sub> = 700 mA, V <sub>IN</sub> = V <sub>BIAS</sub> (Notes 5, 6)   | $V_{DO}$                 |                                       | 1.1        | 1.5  | V             |
| Output Current Limit              | V <sub>OUT</sub> = 90% V <sub>OUT(NOM)</sub>  | I <sub>CL</sub>          | 800                                   | 1450       | 2000 | mA            |
| SNS/ADJ Pin Operating<br>Current  |   | I <sub>SNS</sub>         |                                       | 0.1        | 0.5  | μА            |
| Bias Pin Quiescent<br>Current     | $V_{BIAS} = 2.7 \text{ V}, I_{OUT} = 0 \text{ mA}$  | I <sub>BIASQ</sub>       |                                       | 70         | 110  | μΑ            |
| Bias Pin Disable Current          | V <sub>EN</sub> ≤ 0.4 V   | I <sub>BIAS(DIS)</sub>   |                                       | 0.5        | 1    | μΑ            |
| Input Pin Disable Current         | V <sub>EN</sub> ≤ 0.4 V   | I <sub>VIN(DIS)</sub>    |                                       | 0.5        | 1    | μΑ            |
| EN Pin Threshold Voltage          | EN Input Voltage "H"  | V <sub>EN(H)</sub>       | 0.9                                   |            |      | V             |
|                                   | EN Input Voltage "L"  | V <sub>EN(L)</sub>       |                                       |            | 0.4  |               |
| EN Pull Down Current              | V <sub>EN</sub> = 5.5 V   | I <sub>EN</sub>          |                                       | 0.3        | 1    | μΑ            |
| Power Supply Rejection<br>Ratio   | $V_{IN}$ to $V_{OUT}$ , f = 1 kHz, $I_{OUT}$ = 10 mA, $V_{IN} \ge V_{OUT}$ +0.5 V, $V_{OUT(NOM)}$ = 1.2 V, $V_{BIAS}$ = 3.0 V   | PSRR(V <sub>IN</sub> )   |                                       | 75         |      | dB            |
|                                   | $V_{BIAS}$ to $V_{OUT}$ , f = 1 kHz, $I_{OUT}$ = 10 mA, $V_{IN} \ge V_{OUT}$ +0.5 V, $V_{OUT(NOM)}$ = 1.2 V, $V_{BIAS}$ = 3.0 V   | PSRR(V <sub>BIAS</sub> ) |                                       | 80         |      | dB            |
| Output Noise Voltage              | $V_{IN} = V_{OUT}$ +0.5 V, f = 10 Hz to 100 kHz,<br>$V_{OUT(NOM)}$ = 1.2 V  | V <sub>N</sub>           |                                       | 40         |      | $\mu V_{RMS}$ |
| Thermal Shutdown                  | Temperature increasing  |                          |                                       | 160        |      | °C            |
| Threshold                         | Temperature decreasing  |                          |                                       | 140        |      |               |
| Output Discharge<br>Pull-Down     | V <sub>EN</sub> ≤ 0.4 V, V <sub>OUT</sub> = 0.5 V,<br>NCP136A and NCP136C option  | R <sub>DISCH</sub>       |                                       | 150        |      | Ω             |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>4.</sup> Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.

Dropout voltage is characterized when V<sub>OUT</sub> falls 3% below V<sub>OUT(NOM)</sub>.
 For fixed output voltages below 1.5 V, V<sub>BIAS</sub> dropout does not apply due to a minimum Bias operating voltage of 2.5 V.

**ELECTRICAL CHARACTERISTICS**  $-40^{\circ}\text{C} \le \text{TJ} \le 85^{\circ}\text{C}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $V_{EN} = 1 \text{ V}$ ,  $C_{IN} = 4.7 \text{ }\mu\text{F}$ ,  $C_{OUT} = 10 \text{ }\mu\text{F}$ ,  $C_{BIAS} = 1 \text{ }\mu\text{F}$ . Typical values are at  $T_J = +25^{\circ}\text{C}$ . Min/Max values are for  $-40^{\circ}\text{C} \le T_J \le 85^{\circ}\text{C}$  unless otherwise noted. (Note 7)

| Parameter     | Test conditions  |                         | Symbol             | Min | Тур | Max | Unit |
|---------------|--|-------------------------|--------------------|-----|-----|-----|------|
| NCP136xFCRC0  | <b>40T2G</b> V <sub>BIAS</sub> = 3 V, V <sub>IN</sub> = 0.6 V                      |                         | •                  | •   | •   | •   |      |
| Delay time    | From assertion of V <sub>EN</sub> to output voltage increase                       | 'A' option              | t <sub>DELAY</sub> |     | 73  |     | μs   |
| Rise time     | V <sub>OUT</sub> rise from 10% to 90% V <sub>OUT(NOM)</sub>                        | 'A' option              | t <sub>RISE</sub>  |     | 15  |     |      |
| Turn-On Time  | From assertion of V <sub>EN</sub> to V <sub>OUT</sub> = 98% V <sub>OUT</sub> (NOM) | 'A' option              | t <sub>ON</sub>    |     | 98  |     |      |
| NCP136xFCT080 | T2G & NCP136xFCRC080T2G $V_{BIAS} = 3 V_{,}$                                       | V <sub>IN</sub> = 1.0 V |                    |     |     |     |      |
| Delay time    | From assertion of V <sub>EN</sub> to output voltage increase                       | 'A' and 'B' option      | t <sub>DELAY</sub> |     | 55  |     | μs   |
| Rise time     | V <sub>OUT</sub> rise from 10% to 90% V <sub>OUT(NOM)</sub>                        | 'A' and 'B' option      | t <sub>RISE</sub>  |     | 17  |     | 1    |
| Turn-On Time  | From assertion of V <sub>EN</sub> to V <sub>OUT</sub> = 98% V <sub>OUT</sub> (NOM) | 'A' and 'B' option      | t <sub>ON</sub>    |     | 80  |     |      |
| NCP136xFCT088 | <b>BT2G</b> $V_{BIAS} = 3 \text{ V}, V_{IN} = 1.1 \text{ V}$                       |                         |                    |     |     |     |      |
| Delay time    | From assertion of V <sub>EN</sub> to output voltage increase                       | 'A' option              | t <sub>DELAY</sub> |     | 71  |     | μs   |
| Rise time     | V <sub>OUT</sub> rise from 10% to 90% V <sub>OUT(NOM)</sub>                        | 'A' option              | t <sub>RISE</sub>  |     | 16  |     | 1    |
| Turn-On Time  | From assertion of V <sub>EN</sub> to V <sub>OUT</sub> = 98% V <sub>OUT</sub> (NOM) | 'A' option              | t <sub>ON</sub>    |     | 97  |     |      |
| NCP136xFCT105 | $ST2G V_{BIAS} = 3 V, V_{IN} = 1.25 V$   |                         |                    |     |     |     |      |
| Delay time    | From assertion of V <sub>EN</sub> to output voltage increase                       | 'A' option              | t <sub>DELAY</sub> |     | 71  |     | μs   |
| Rise time     | V <sub>OUT</sub> rise from 10% to 90% V <sub>OUT(NOM)</sub>                        | 'A' option              | t <sub>RISE</sub>  |     | 18  |     |      |
| Turn-On Time  | From assertion of $V_{EN}$ to $V_{OUT} = 98\% V_{OUT(NOM)}$                        | 'A' option              | t <sub>ON</sub>    |     | 102 |     |      |
| NCP136xFCT110 | <b>T2G</b> V <sub>BIAS</sub> = 3 V, V <sub>IN</sub> = 1.3 V                        |                         |                    |     |     |     |      |
| Delay time    | From assertion of V <sub>EN</sub> to output voltage increase                       | 'A' option              | t <sub>DELAY</sub> |     | 71  |     | μs   |
| Rise time     | V <sub>OUT</sub> rise from 10% to 90% V <sub>OUT(NOM)</sub>                        | 'A' option              | t <sub>RISE</sub>  |     | 19  |     | 1    |
| Turn-On Time  | From assertion of V <sub>EN</sub> to V <sub>OUT</sub> = 98% V <sub>OUT</sub> (NOM) | 'A' option              | t <sub>ON</sub>    |     | 105 |     |      |
| NCP136xFCT120 | $V_{BIAS} = 3 \text{ V}, V_{IN} = 1.4 \text{ V}$                                   |                         |                    |     |     |     |      |
| Delay time    | From assertion of V <sub>EN</sub> to   | 'A' option              | t <sub>ON</sub>    |     | 70  |     | μs   |
|               | output voltage increase  | 'C' option              |                    |     | 80  |     | ]    |
| Rise time     | V <sub>OUT</sub> rise from 10% to 90% V <sub>OUT(NOM)</sub>                        | 'A' option              | t <sub>RISE</sub>  |     | 21  |     | ]    |
|               |  | 'C' option              |                    |     | 80  |     | ]    |
| Turn-On Time  | From assertion of V <sub>EN</sub> to V <sub>OUT</sub> = 98% V <sub>OUT</sub> (NOM) | 'A' option              | ton                |     | 108 |     |      |
|               | - 001 - 55,5 + 001 (NOM)   | 'C' option              |                    |     | 210 |     |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>7.</sup> Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.

#### **TYPICAL CHARACTERISTICS**

At T<sub>J</sub> = +25°C, V<sub>IN</sub> = V<sub>OUT(NOM)</sub> + 0.3 V, V<sub>BIAS</sub> = 2.8 V, V<sub>EN</sub> = V<sub>BIAS</sub>, V<sub>OUT(NOM)</sub> = 1.2 V, I<sub>OUT</sub> = 700 mA, C<sub>IN</sub> = 4.7  $\mu$ F, C<sub>BIAS</sub> = 1  $\mu$ F, and C<sub>OUT</sub> = 10  $\mu$ F (effective capacitance), unless otherwise noted.

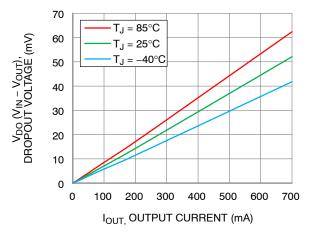


Figure 4. V<sub>IN</sub> Dropout Voltage vs. I<sub>OUT</sub> and T<sub>J</sub>

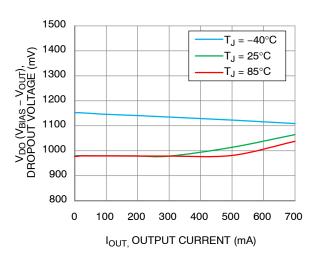


Figure 6. V<sub>BIAS</sub> Dropout Voltage vs. I<sub>OUT</sub> and T<sub>J</sub>

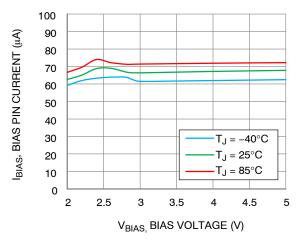


Figure 8. BIAS Pin Current vs. VBIAS and TJ

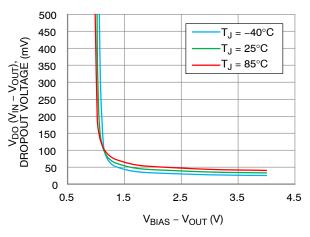


Figure 5. V<sub>IN</sub> Dropout Voltage vs. V<sub>BIAS</sub> – V<sub>OUT</sub> and T<sub>J</sub>

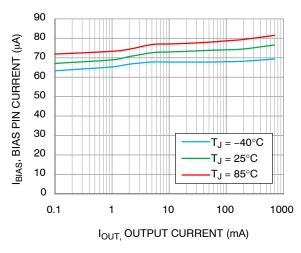


Figure 7. BIAS Pin Current vs. I<sub>OUT</sub> and T<sub>J</sub>

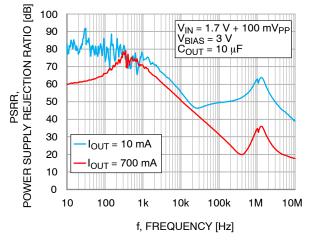
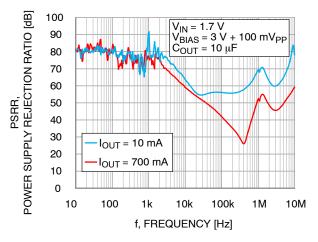


Figure 9. V<sub>IN</sub> PSRR vs. Frequency

#### TYPICAL CHARACTERISTICS (continued)

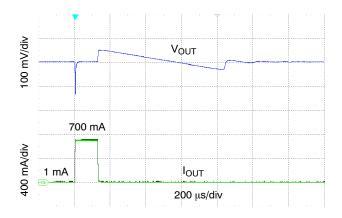
At T<sub>J</sub> = +25°C,  $V_{IN}$  =  $V_{OUT(NOM)}$  + 0.3 V,  $V_{BIAS}$  = 2.8 V,  $V_{EN}$  =  $V_{BIAS}$ ,  $V_{OUT(NOM)}$  = 1.2 V,  $I_{OUT}$  = 700 mA,  $C_{IN}$  = 4.7  $\mu$ F,  $C_{BIAS}$  = 1  $\mu$ F, and  $C_{OUT}$  = 10  $\mu$ F (effective capacitance), unless otherwise noted.



SPECTRAL NOISE DENSITY [µV/sqrtHz] 10  $V_{IN}$  = 1.7 V  $V_{BIAS}$  = 2.8 V  $C_{OUT}$  = 10  $\mu F$ 1 0.1 I<sub>OUT</sub> = 1 mA 0.01 I<sub>OUT</sub> = 700 mA 0.001 10 10k 100k 10M 100 1M FREQUENCY [Hz]

Figure 10.  $V_{\mbox{\footnotesize BIAS}}$  PSRR vs. Frequency

Figure 11. Output Voltage Spectral Noise Density vs. Frequency



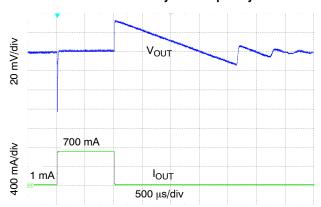


Figure 12. Load Transient Response,  $I_{OUT}$  = 1 mA to 700 mA in 1  $\mu$ s,  $C_{OUT}$  = 10  $\mu$ F

Figure 13. Load Transient Response,  $I_{OUT}$  = 1 mA to 700 mA in 1  $\mu$ s,  $C_{OUT}$  = 47  $\mu$ F

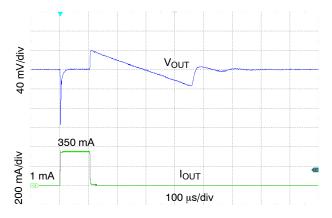


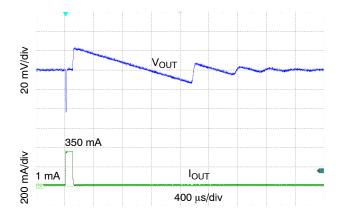


Figure 14. Load Transient Response,  $I_{OUT}$  = 1 mA to 350 mA in 1  $\mu s,\,C_{OUT}$  = 4.7  $\mu F$ 

Figure 15. Load Transient Response,  $I_{OUT}$  = 1 mA to 350 mA in 1  $\mu$ s,  $C_{OUT}$  = 10  $\mu$ F

#### TYPICAL CHARACTERISTICS (continued)

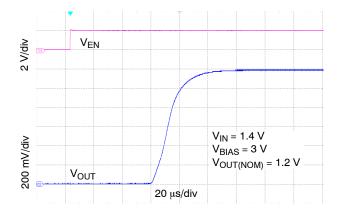
At T<sub>J</sub> = +25°C,  $V_{IN}$  =  $V_{OUT(NOM)}$  + 0.3 V,  $V_{BIAS}$  = 2.8 V,  $V_{EN}$  =  $V_{BIAS}$ ,  $V_{OUT(NOM)}$  = 1.2 V,  $I_{OUT}$  = 700 mA,  $C_{IN}$  = 4.7  $\mu$ F,  $C_{BIAS}$  = 1  $\mu$ F, and  $C_{OUT}$  = 10  $\mu$ F (effective capacitance), unless otherwise noted.



V<sub>EN</sub>
V<sub>OUT</sub>
V<sub>OUT</sub>
V<sub>IN</sub> = 1.4 V
V<sub>BIAS</sub> = 3 V
V<sub>OUT</sub>(NOM) = 1.2 V
20 μs/div

Figure 16. Load Transient Response,  $I_{OUT}$  = 1 mA to 350 mA in 1  $\mu s,\,C_{OUT}$  = 47  $\mu F$ 

Figure 17. Enable Transient Response,  $C_{OUT}$  = 10  $\mu$ F,  $I_{OUT}$  = 700 mA – A Option (Normal)



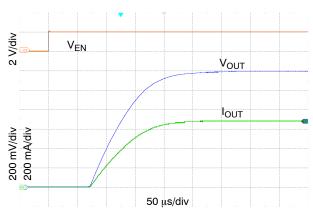
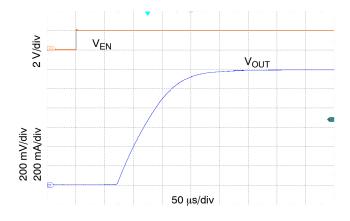


Figure 18. Enable Transient Response,  $C_{OUT}$  = 10  $\mu F$ ,  $I_{OUT}$  = 0 mA - A Option (Normal)

Figure 19. Enable Transient Response,  $C_{OUT}$  = 10  $\mu$ F,  $I_{OUT}$  = 700 mA – C Option (Slow)



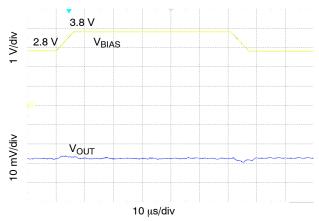


Figure 20. Enable Transient Response, C<sub>OUT</sub> = 10 μF, I<sub>OUT</sub> = 0 mA – C Option (Slow)

Figure 21. BIAS Line Transient Response,  $V_{BIAS}$  = 2.8 V to 3.8 V in 5  $\mu s$ 

#### TYPICAL CHARACTERISTICS (continued)

At T<sub>J</sub> = +25°C,  $V_{IN}$  =  $V_{OUT(NOM)}$  + 0.3 V,  $V_{BIAS}$  = 2.8 V,  $V_{EN}$  =  $V_{BIAS}$ ,  $V_{OUT(NOM)}$  = 1.2 V,  $I_{OUT}$  = 700 mA,  $C_{IN}$  = 4.7  $\mu$ F,  $C_{BIAS}$  = 1  $\mu$ F, and  $C_{OUT}$  = 10  $\mu$ F (effective capacitance), unless otherwise noted.

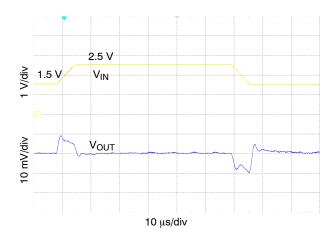


Figure 22. IN Line Transient Response,  $V_{IN}$  = 1.5 V to 2.5 V in 5  $\mu s$ 

#### **APPLICATIONS INFORMATION**

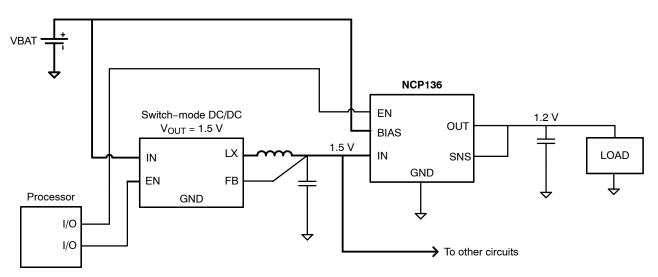


Figure 23. Typical Application: Low-Voltage DC/DC Post-Regulator with ON/OFF Functionality

The NCP136 dual-rail very low dropout voltage regulator is using NMOS pass transistor for output voltage regulation from  $V_{\rm IN}$  voltage. All the low current internal control circuitry is powered from the  $V_{\rm BIAS}$  voltage.

The use of an NMOS pass transistor offers several advantages in applications. Unlike PMOS topology devices, the output capacitor has reduced impact on loop stability. Vin to Vout operating voltage difference can be very low compared with standard PMOS regulators in very low Vin applications.

The NCP136 offers smooth monotonic start-up. The controlled voltage rising limits the inrush current.

The Enable (EN) input is equipped with internal hysteresis. NCP136 Voltage linear regulator Fixed version is available.

#### **Dropout Voltage**

Because of two power supply inputs  $V_{IN}$  and  $V_{BIAS}$  and one  $V_{OUT}$  regulator output, there are two Dropout voltages specified.

The first, the  $V_{IN}$  Dropout voltage is the voltage difference ( $V_{IN}-V_{OUT}$ ) when  $V_{OUT}$  starts to decrease by percent specified in the Electrical Characteristics table.  $V_{BIAS}$  is high enough; specific value is published in the Electrical Characteristics table.

The second,  $V_{BIAS}$  dropout voltage is the voltage difference ( $V_{BIAS}-V_{OUT}$ ) when  $V_{IN}$  and  $V_{BIAS}$  pins are joined together and  $V_{OUT}$  starts to decrease.

#### **Input and Output Capacitors**

The NCP136 device is designed to be stable for ceramic output capacitors with Effective capacitance in the range from 4.7  $\mu$ F to 47  $\mu$ F. The device is also stable with multiple capacitors in parallel, having the total effective capacitance in the specified range.

In applications where no low input supplies impedance available (PCB inductance in  $V_{IN}$  and/or  $V_{BIAS}$  inputs as example), the recommended  $C_{IN}=1\,\mu F$  and  $C_{BIAS}=0.1\,\mu F$  or greater. Ceramic capacitors are recommended. For the best performance all the capacitors should be connected to the NCP136 respective pins directly in the device PCB copper layer, not through vias having not negligible impedance.

When using small ceramic capacitor, their capacitance is not constant but varies with applied DC biasing voltage, temperature and tolerance. The effective capacitance can be much lower than their nominal capacitance value, most importantly in negative temperatures and higher LDO output voltages. That is why the recommended Output capacitor capacitance value is specified as Effective value in the specific application conditions.

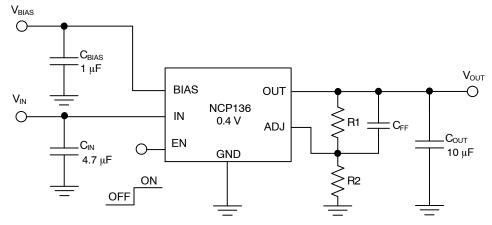


Figure 24. Typical Application Schematic - Adjustable

#### **Output Voltage Adjustment**

The required output voltage can be adjusted from 0.4 V to 3.0 V using two external resistors. Typical application schematics is shown in Figure 24. Output voltage is calculated according to equation 1. Generally, any voltage option can used as adjustable, in the equation below  $V_{OUT-ADJ}$  is requested voltage and  $V_{OUT\_NOM}$  is nominal  $V_{OUT}$  as reference voltage. When resistor's value is in  $k\Omega$  range last term  $(I_{ADJ}\cdot R_1)$  can be omitted because its effect on output voltage accuracy is negligible. In other cases it should be consider especially when tight output voltage accuracy is requested.

$$V_{OUT-ADJ} = V_{OUT\_NOM} \cdot \left(1 + \frac{R_1}{R_2}\right) + I_{ADJ} \cdot R_1$$
 (eq. 1)

*Voltage Calculation Example – V\_{OUT} = 0.8 \ V:* 

a. 
$$R_1 = R_2 = 5.1 \text{ k}\Omega$$
, no  $(I_{FB} \times R_1)$   
 $V_{OUT-ADJ} = 0.4 \cdot (1 + 5.1 \text{ k}\Omega/5.1 \text{ k}\Omega) = 0.8 \text{ V}$   
Error  $-0\%$ 

b. 
$$R_1 = R_2 = 5.1 \text{ k}\Omega$$
  
 $V_{OUT-ADJ} = 0.4 \cdot (1 + 5.1 \text{ k}\Omega/5.1 \text{ k}\Omega) + 100 \text{ nA} \cdot 5.1 \text{ k}\Omega = 0.80051 \text{ V}$   
Error  $-0.06\%$ 

c. 
$$R_1 = R_2 = 51 \text{ k}\Omega$$
  
 $V_{OUT-ADJ} = 0.4 \cdot (1 + 51 \text{ k}\Omega/51 \text{ k}\Omega) + 100 \text{ n}A \cdot 51 \text{ k}\Omega = 0.8051 \text{ V}$   
 $Error - 0.63\%$ 

It is recommended to keep the total resistance of resistors (R1 + R2) no greater than a few hundred  $k\Omega$ . If total resistance is too big the dynamic performance could get worse due to PCB parasitic capacitance. Big resistors value in combination with parasitic capacitance create low–pass filter and virtually slow–down LDO control loop.

Output Voltage Example:

| V <sub>OUT</sub> (V) | R <sub>1</sub> (kΩ) <sup>(Note 1)</sup> | R <sub>2</sub> (kΩ) <sup>(Note 1)</sup> | C <sub>FF</sub> (nF) |
|----------------------|---|---|----------------------|
| 0.80                 | 5.1                                     | 5.1                                     | 5.6                  |
| 1.05                 | 3.9                                     | 2.4                                     | 5.6                  |
| 1.10                 | 8.2                                     | 4.7                                     | 5.6                  |

To increase power efficiency, current flows through resistor divider can be reduced by multiply all resistor values by 10.

#### Feed Forward Capacitor CFF

Feedforward capacitor is recommended to improve PSRR, load transient and noise performance. Recommended value for NCP136 device is about 5.6 nF. The capacitor can also improve LDO stability.

#### **Enable Operation**

The enable pin will turn the regulator on or off. The threshold limits are covered in the electrical characteristics table in this data sheet. To get the full functionality of Soft Start, it is recommended to turn on the  $V_{IN}$  and  $V_{BIAS}$  supply voltages first and activate the Enable pin no sooner than  $V_{IN}$  and  $V_{BIAS}$  are on their nominal levels. If the enable function is not to be used then the pin should be connected to  $V_{IN}$  or  $V_{BIAS}$ .

If the EN pin voltage is < 0.4 V the device is guaranteed to be disabled. The pass transistor is turned off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active (devices with Output Active Discharge feature only) so that the output voltage  $V_{OUT}$  is pulled down to GND through a 150  $\Omega$  resistor. In the disable state the device consumes as low as typ. 0.5  $\mu A$  from the  $V_{IN}$  and 0.5  $\mu A$  from  $V_{BIAS}$ . If the EN pin voltage > 0.9 V the device is guaranteed to be enabled. The NCP136 regulates the output voltage and the active discharge transistor is turned off. The EN pin has internal pull–down

current source with typ. value of  $0.3~\mu A$  which assures that the device is turned off when the EN pin is not connected.

#### **Current Limitation**

The internal Current Limitation circuitry allows the device to supply the full nominal current and surges but protects the device against Current Overload or Short.

#### **Thermal Protection**

Internal thermal shutdown (TSD) circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When TSD activated, the regulator output turns off. When cooling down under the low temperature threshold, device output is activated again. This TSD feature is provided to prevent failures from accidental overheating.

Activation of the thermal protection circuit indicates excessive power dissipation or inadequate heatsinking. For reliable operation, junction temperature should be limited to +105°C maximum.

#### ORDERING INFORMATION

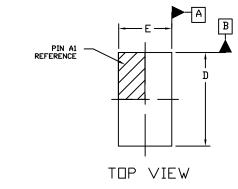
| Device            | Nominal Output<br>Voltage | Marking | Option  | Package                           | Shipping <sup>†</sup> |
|-------------------|---------------------------|---------|---|-----------------------------------|-----------------------|
| NCP136AFCT080T2G  | 0.80 V                    | 7A      | Output Active Discharge,<br>Normal Turn-On Slew Rate                      |                                   |                       |
| NCP136BFCT080T2G  | 0.80 V                    | 7H      | Non – Active Discharge,<br>Normal Turn-On Slew Rate                       |                                   |                       |
| NCP136AFCT088T2G  | 0.88 V                    | 7J      | Output Active Discharge,<br>Normal Turn-On Slew Rate                      |                                   |                       |
| NCP136AFCT105T2G  | 1.05 V                    | 7K      | Output Active Discharge,<br>Normal Turn-On Slew Rate                      | WLCSP6<br>Case 567XK<br>(Pb-Free) | 5000 / Tape & Reel    |
| NCP136AFCT110T2G  | 1.10 V                    | 7L      | Output Active Discharge,<br>Normal Turn-On Slew Rate                      | (1.5.1166)                        |                       |
| NCP136AFCT120T2G  | 1.20 V                    | 7E      | Output Active Discharge,<br>Normal Turn-On Slew Rate                      |                                   |                       |
| NCP136CFCT120T2G  | 1.20 V                    | 7C      | Output Active Discharge,<br>Slow Turn-On Slew Rate                        |                                   |                       |
| NCP136AFCRC040T2G | 0.40 V                    | 7M      | Output Active Discharge,<br>Normal Turn-On Slew Rate<br>Back Side Coating | WLCSP6<br>Case 567YU              | 5000 / Tara & David   |
| NCP136AFCRC080T2G | 0.80 V                    | 7A      | Output Active Discharge,<br>Normal Turn-On Slew Rate<br>Back Side Coating | (Pb-Free)                         | 5000 / Tape & Reel    |

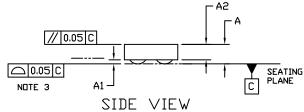
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

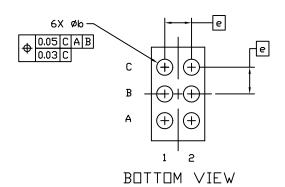
To order other package and voltage variants, please contact your ON Semiconductor sales representative.

#### WLCSP6 1.4x0.8x0.33 CASE 567XK ISSUE O

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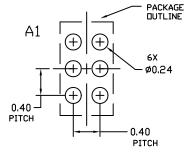




#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

|     | MILLIMETERS |       |       |  |  |
|-----|-------------|-------|-------|--|--|
| DIM | MIN.        | N□M.  | MAX.  |  |  |
| Α   |             | 1     | 0.33  |  |  |
| A1  | 0.040       | 0.060 | 0.080 |  |  |
| A2  | 0.23 REF    |       |       |  |  |
| Ø   | 0.220       | 0.240 | 0.260 |  |  |
| D   | 1.370       | 1.400 | 1.430 |  |  |
| E   | 0.770       | 0.800 | 0.830 |  |  |
| e   | 0.40 BSC    |       |       |  |  |



RECOMMENDED MOUNTING FOOTPRINT

## GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Month Code

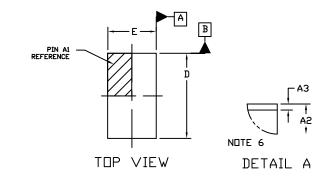
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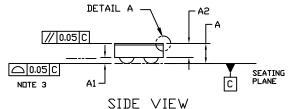
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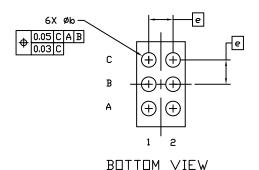
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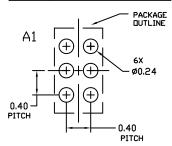
XX = Specific Device CodeM = Month Code

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#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
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- DATUM C, THE SEATING PLANE, IS DEFINED BY THE SPHERICAL CROWNS OF THE SOLDER BALLS.
- 5. DIMENSION 6 IS MEASURED AT THE MAXIMUM SOLDER BALL DIAMETER PARALLEL TO DATUM C.
- 6. BACKSIDE COATING IS OPTIONAL.

|     | MILLIMETERS |       |       |  |
|-----|-------------|-------|-------|--|
| DIM | MIN.        | N□M.  | MAX.  |  |
| Α   |             | 0.330 | 0.370 |  |
| A1  | 0.080       | 0.100 | 0.120 |  |
| A2  | 0.230 REF   |       |       |  |
| A3  | 0.020       | 0.025 | 0.030 |  |
| b   | 0.220       | 0.240 | 0.260 |  |
| D   | 1.370       | 1.400 | 1.430 |  |
| Ε   | 0.770       | 0.800 | 0.830 |  |
| e   | 0.400 BSC   |       |       |  |



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